

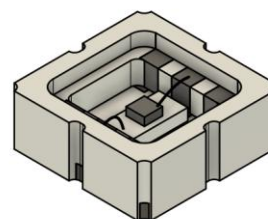
**200 μ m InGaAs APD (Type 5)****(P/N.: Ain-200-05-01)****Features**

- Excellent linearity, high power handling (0dBm) and high gain ($M = 10 - 20$) InGaAs APD.
- Typical operating voltage 8V ($M = 10$) below the breakdown voltage.
- Active Area = 200 μ m.

Applications

- High performance laser range finding
- Scientific instrumentation

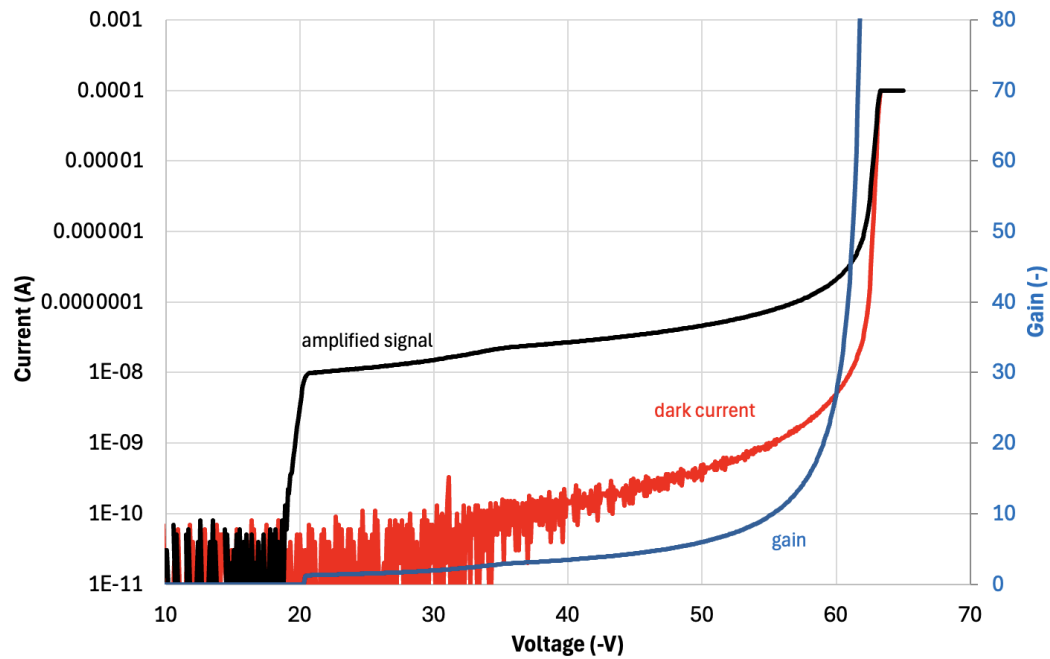
3D view (w/o glass)

**Absolute Maximum Ratings**

Parameter	Symbol	Min	Typ	Max	Unit
Forward Current	I_F	-	-	1	mA
Reverse Voltage	V_R	-	-	$0.99 \times V_{BR}$	V
CW input power	P_{MAX-CW}	-	-	1	mW
Operating Case Temperature	T_C	-40	-	85	$^{\circ}C$
Storage Temperature	T_{STG}	-55	-	85	$^{\circ}C$

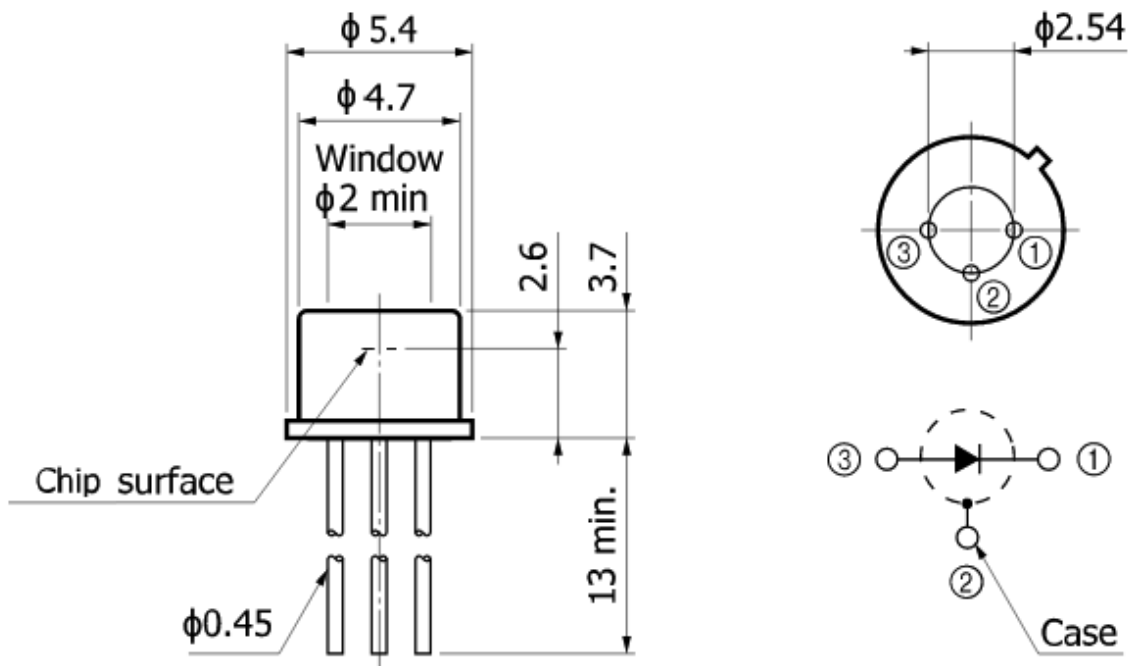
Opto-Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Wavelength Range	λ	1000		1630	nm	
Reverse Breakdown Voltage	V_{BR}	50	63	83	V	$I_D = 10\mu A$
Operating Voltage	V_{OP}	43	55	75	V	$M = 10$
Multiplication Factor	M	-	10	-		$V_{OP} = V_{BR} - 8V$
		-	20	-		$V_{OP} = V_{BR} - 3V$
Spectral Responsivity	S	0.85	0.9	0.95	A/W	1550nm, $M = 1$
Multiplied Dark Current	I_{DM}	-	8	25	nA	$M = 10$
Terminal Capacitance	C_J	-	1.5	2	pF	$M = 10$
Bandwidth	BW	1	1.5	2	GHz	$M = 10$
Temperature coeff of V_{BR}	$\Delta V/\Delta T$	-	0.075	-	V/ $^{\circ}C$	$T = 25^{\circ}C$
Excess Noise Factor	F	-	3.2	3.7		$M = 10$
		-	5.5	6.0		$M = 20$
Noise Equivalent Current	NEP	-	0.03	0.1	fA/Hz ^{0.5}	$M = 10$



Dimensional outlines (unit = mm)

TO

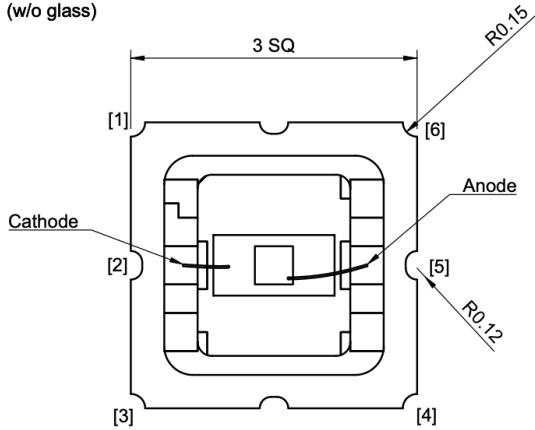


Package can be customized

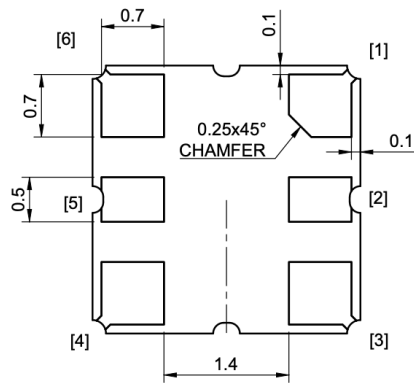


SMD

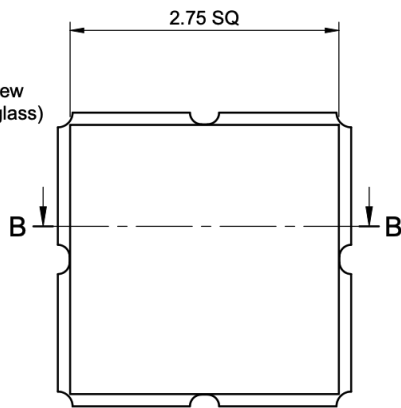
Top view
(w/o glass)



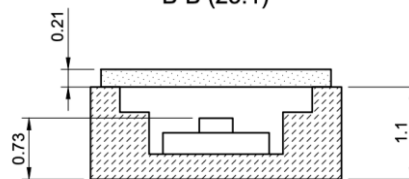
Bottom view



Top view
(with glass)



B-B (25:1)



Package can be customized